



PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of

Docket No: Q56320

Kaoru NARITA

Appln. No.: 09/421,273

Group Art Unit: 2823

Confirmation No.: 3894

Examiner: J. Garcia

Filed: October 20, 1999

For: SEMICONDUCTOR DEVICE HAVING PROTECTION CIRCUIT IMPLEMENTED BY BIPOLAR TRANSISTOR FOR DISCHARGING STATIC CHARGE CURRENT AND PROCESS OF FABRICATION

AMENDMENT UNDER 37 C.F.R. § 1.111

Commissioner for Patents
Washington, D.C. 20231

Sir:

In response to the Office Action dated January 13, 2003, please amend the above-identified application as follows:

IN THE CLAIMS:

Please enter the following amended claims:

1. (*Thrice Amended*) A semiconductor device comprising:
- a semiconductor substrate of one conductivity type;
 - shallow trench isolating regions having a first depth, and disposed in surface portions of said semiconductor substrate and defining active areas therebetween;
 - a first terminal connected to one of said active areas;
 - a second terminal connected to another of said active areas;
 - a circuit component connected between said first terminal and said second terminal; and

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Amend
J. Garcia
4/10/03